

N-Channel Enhancement Mode Power MOSFET

Description

SMIRF18N50 is an N-channel enhancement mode power MOS field effect transistor. The improved planar stripe cell and the improved guard ring terminal have been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are widely used in AC-DC power suppliers, DCDC converters and H-bridge PWM motor drivers.

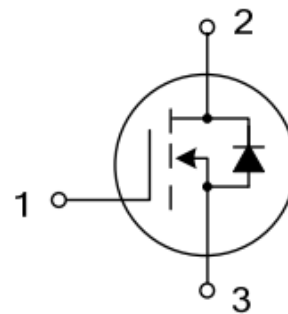
General Features

- 18A, 500V, $R_{DS(on)(typ.)} = 0.28\Omega @ V_{GS}=10V$
- Low Gate charge
- Low Crss
- Fast Switching
- Improved dv/dt Capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

I_D	18A
V_{DSS}	500V
$R_{dson (max)}$	$0.35\Omega (V_{GS}=10V, I_D=9A)$
Q_g	60nC



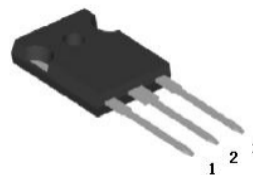
1.Gate 2.Drain 3.Source



TO-220



TO-220F



TO-247

Order Information

Order Information	Marking ID	Package	Packing Type Supplied As
SMIRF18N50T2TL	IRF18N50	TO220F-3L	1000 units on Box, 5000 units on Carton
SMIRF18N50T1TL	IRF18N50	TO220-3L	1000 units on Box, 5000 units on Carton
SMIRF18N50T8TL	IRF18N50	TO247-3L	450 units on Box, 2250 units on Carton

Absolute Maximum Ratings Ta=25 °C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source Voltage	V _{DS}	500	V
Gate-source Voltage	V _{GS}	±30	V
Continuous Drain Current(Ta=25°C)	I _D	18	A
Drain Current-Pulsed	I _{DM}	72	A
Total Dissipation(Ta=25°C)	TO247	256	W
	TO220	185	
	TO220F	65	
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55 to 150	°C
Single Pulse Avalanche Energy	E _{AS}	990	mJ
ESD HBM(Human Body Mode)		≥2000	V
ESD MM(Machine Mode)		≥200	V

Electrical Characteristics Ta = 25°C

PARAMETER	Symbol	Test Condition	MIN	TYP	MAX	UNIT
Drain-source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	500			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250μA	3.0		5.0	V
Drain-source Leakage Current	I _{DSS}	V _{DS} =500V, V _{GS} =0V			10	μA
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =18A			1.5	V
Gate-body Leakage Current (V _{DS} = 0)	I _{GSS}	V _{GS} =±30V, V _{DS} =0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =9A		0.28	0.35	Ω

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant in temperature etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings

Thermal Characteristics Ta=25°C

PARAMETER		Symbol	TYP	MAX	UNIT
Maximum Junction-to-case	TO220F, TO220	R _{QJC}		1.92	°C/W
	TO-247			0.32	
Maximum Junction-to-Ambient	TO220F, TO220	R _{QJA}		80	
	TO247			40	

Note1: Ensure that the channel temperature does not exceed 150°C

Note2: V_{DD}=50V, T_{ch}=25 °C(initial), I_{AS}=18A, R_g=25Ω

Note3: This transistor is sensitive to electrostatic and should be handled with care

Dynamic Characteristics Ta = 25 °C

PARAMETER	Symbol	Test Condition	MIN	TYP	MAX	UNIT
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHZ		2550	3990	pF
output Capacitance	C _{oss}			225	300	pF
Reverse Transfer Capacitance	C _{rss}			25	60	pF

Switching Characteristics Ta=25 °C

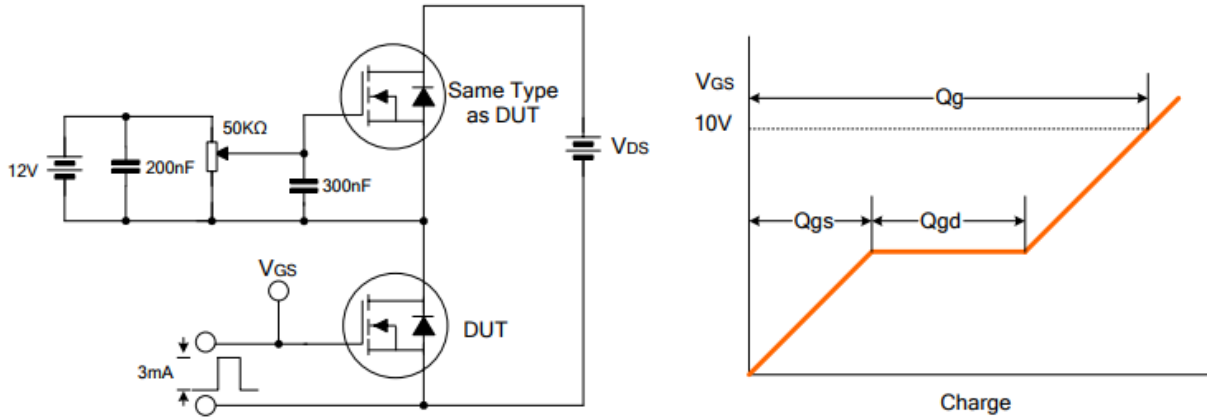
PARAMETER	Symbol	Test Condition	MIN	TYP	MAX	UNIT
Turn-On Delay Time	T _{d(on)}	V _{DS} =250V, I _D =18A, V _{GS} =10V, R _G =25Ω		35	65	nS
Turn-On Rise Time	T _r			85	150	nS
Turn-Off Delay Time	T _{d(off)}			125	250	nS
Turn-Off Rise Time	T _f			85	150	nS
Total Gate Charge	Q _g	V _{DS} =400V, I _D =18A, V _{GS} =10V		45	70	nC
Gate-Source Charge	Q _{gs}			15		nC
Gate-Drain Charge	Q _{gd}			10		nC

Drain-Source Diode Maximum Ratings and Characteristics Ta=25 °C

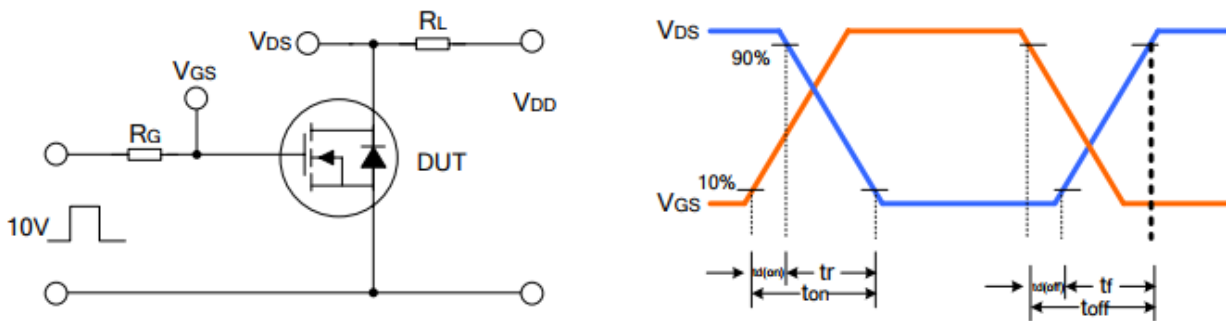
PARAMETER	Symbol	Test Condition	MIN	TYP	MAX	UNIT
Max. Diode Forward Current	I _s	Integral Reverse P-N Junction Diode in the MOSFET			18	A
Pulsed Source Current	I _{sm}				72	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _s =18A			1.5	V
Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _s =18A, dI _F /dt=100A/μs		400		nS
Reverse Recovery Charge	Q _{rr}				3.2	

Test Circuit

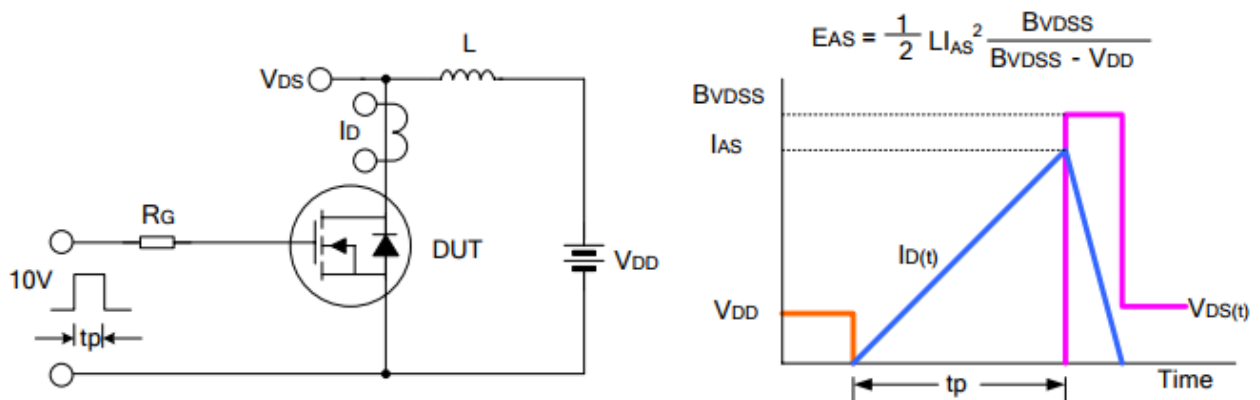
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveform



Typical Characteristics Curve

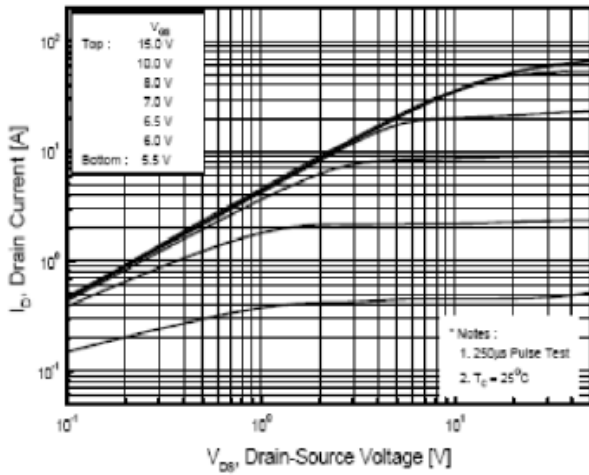


Figure 1: Output Characteristics

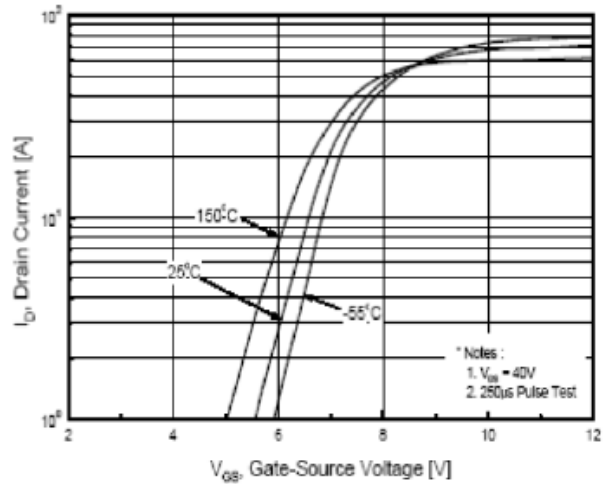


Figure 2: Transfer Characteristics

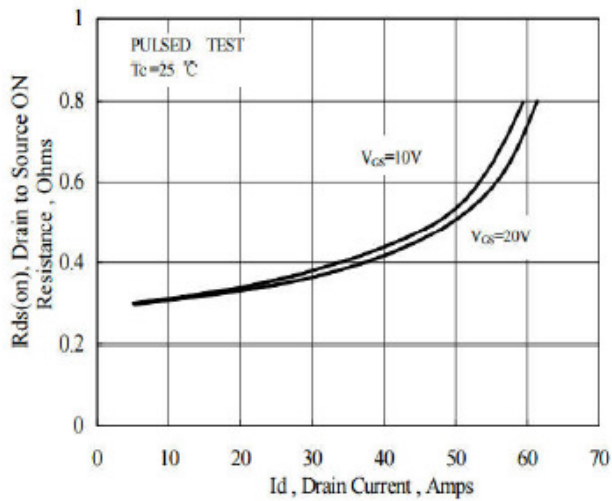
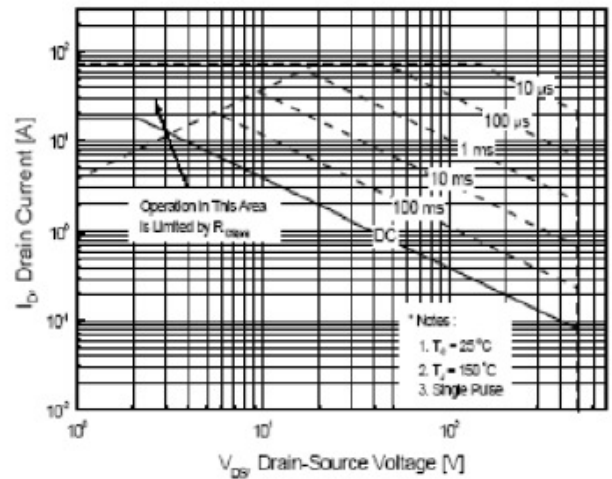
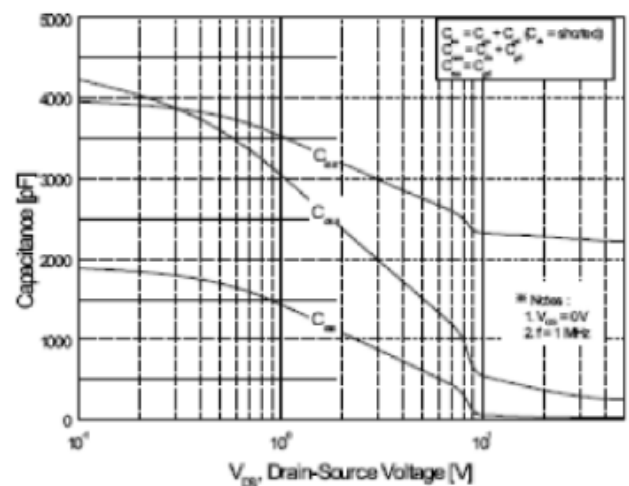
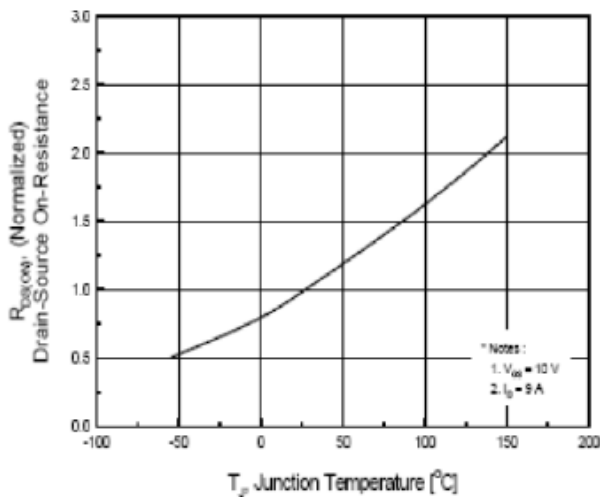


Figure 3: On Resistance Vs Drain Current



Source Voltage

Figure 4: On Resistance Vs Gate



Typical Characteristics Curve

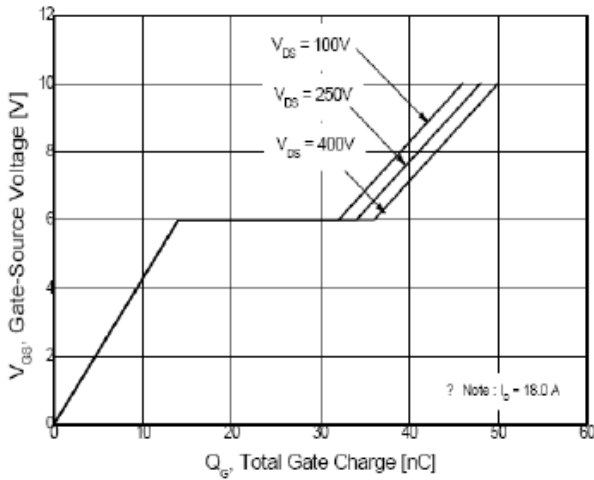


Figure7: Gate Charge Waveform
Diode Forward Voltage

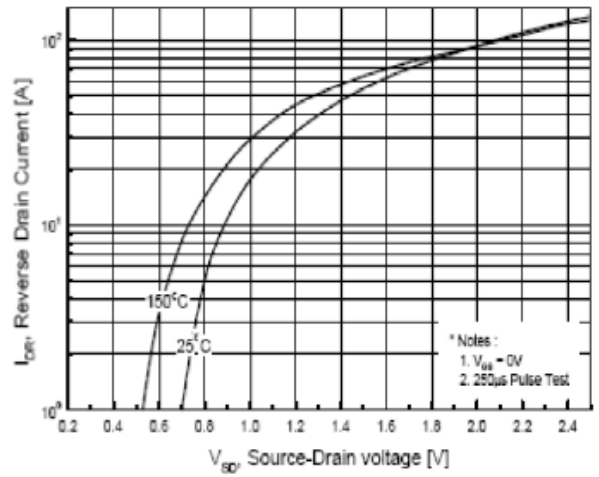


Figure8: Source-Drain

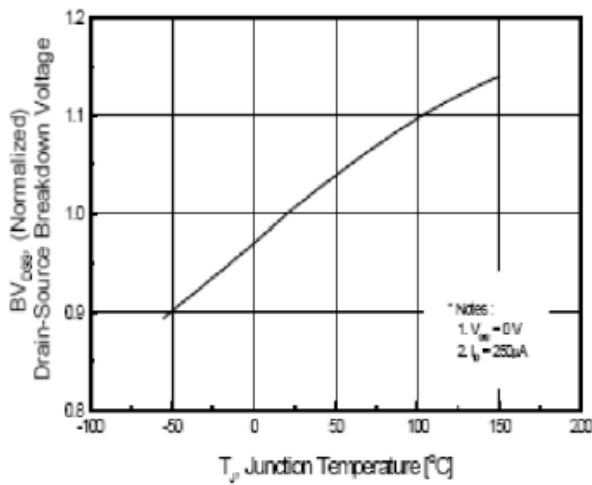
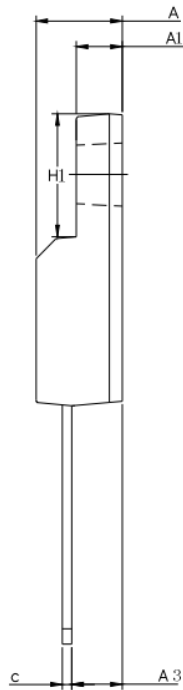
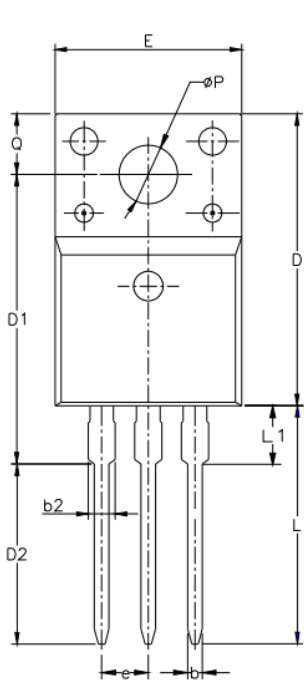


Figure9: Breakdown Voltage Vs Junction Temperature

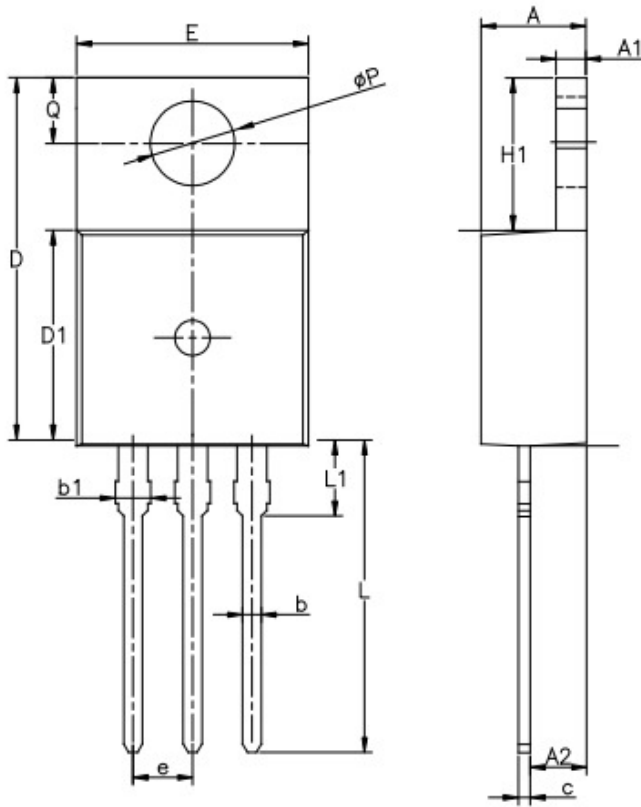
Note: The above characteristics curves are presented for reference only and not guaranteed by production test unless otherwise noted

Outline Information (TO220F-3L)



SYMBOL	MIN	NOM	MAX
A	4.42	4.70	5.02
A1	2.30	2.54	2.80
A3	2.50	2.76	3.10
b	0.70	0.80	0.90
b2	—	—	1.47
c	0.35	0.50	0.65
D	15.25	15.87	16.25
D1	15.30	15.75	16.30
D2	9.30	9.80	10.30
E	9.73	10.16	10.36
e	2.54BCS		
H1	6.40	6.68	7.00
L	12.48	12.98	13.48
L1	/	/	3.50
ϕP	3.00	3.18	3.40
Q	3.05	3.30	3.55

Outline Information (TO220-3L)



SYMBOL	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	1.00	1.30	1.50
A2	1.80	2.40	2.80
b	0.60	0.80	1.00
b1	1.00	—	1.60
c	0.30	—	0.70
D	15.10	15.70	16.10
D1	8.10	9.20	10.00
E	9.60	9.90	10.40
e	2.54BSC		
H1	6.10	6.50	7.00
L	12.60	13.08	13.60
L1	—	—	3.95
ϕP	3.40	3.70	3.90
Q	2.60	—	3.20

Outline Information (TO247-3L)

UNIT: mm

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	4.60		5.15	A1	1.30		1.60
b	2.86		3.26	b1	1.86		2.26
b2		1.20		C		0.50	
D	19.00		21.00	E	15.45		15.75
E1	12.00		13.06	e		5.45	
L	14.00		14.60	L1	5.20		5.88
L2	24.00		24.40	L3	10.00		10.60
P		3.50		Q	2.30		2.70

